

Description

The HSU80N03 is the high cell density trenched N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

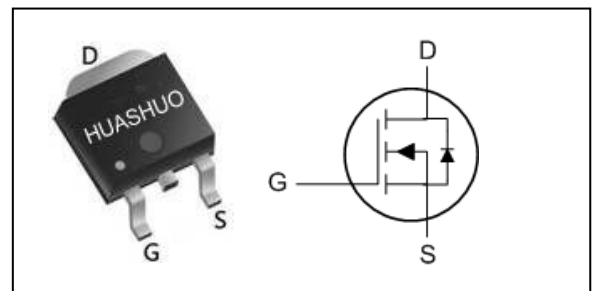
The HSU80N03 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

Product Summary

V _{DS}	30	V
R _{DSON} ,TYP	4.9	mΩ
I _D	80	A

TO252 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		10s	Steady State	
V _{DS}	Drain-Source Voltage	30		V
V _{GS}	Gate-Source Voltage	±20		V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ₁	80		A
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ₁	57		A
I _{DM}	Pulsed Drain Current ₂	320		A
EAS	Single Pulse Avalanche Energy ₃	300		mJ
P _D @T _C =25°C	Total Power Dissipation ₄	115		W
P _D @T _A =25°C	Total Power Dissipation ₄	6	2.4	W
T _{STG}	Storage Temperature Range	-55 to 175		°C
T _J	Operating Junction Temperature Range	-55 to 175		°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient (Steady State) ₁	---	50	°C/W
R _{θJA}	Thermal Resistance Junction-Ambient ₁ (t ≤ 10s)	---	25	°C/W
R _{θJC}	Thermal Resistance Junction-Case ₁	---	0.8	°C/W



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.028	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ₂	V _{GS} =10V, I _D =30A	---	4.9	6	mΩ
		V _{GS} =4.5V, I _D =15A	---	7.5	10	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.0	1.8	3	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-6.16	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =24V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =24V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =30A	20	---	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.7	3.4	Ω
Q _g	Total Gate Charge (4.5V)	V _{DS} =30V, V _{GS} =10V, I _D =40A	---	84	---	nC
Q _{gs}	Gate-Source Charge		---	14	---	
Q _{gd}	Gate-Drain Charge		---	30	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =30V, V _{GS} =10V, R _G =3Ω I _D =40A	---	20	---	ns
T _r	Rise Time		---	15	---	
T _{d(off)}	Turn-Off Delay Time		---	50	---	
T _f	Fall Time		---	8	---	
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1MHz	---	2290	---	pF
C _{oss}	Output Capacitance		---	360	---	
C _{rss}	Reverse Transfer Capacitance		---	280	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current _{1,5}	V _G =V _D =0V, Force Current	---	---	80	A
I _{SM}	Pulsed Source Current _{2,5}		---	---	160	A
V _{SD}	Diode Forward Voltage ₂	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1	V
t _{rr}	Reverse Recovery Time	I _F =40A, di/dt=100A/μs,	---	32	---	nS
Q _{rr}	Reverse Recovery Charge	T _J =25°C	---	60	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The EAS data shows Max. rating. The test condition is V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=53.8A
- 4.The power dissipation is limited by 175°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.



Typical Characteristics

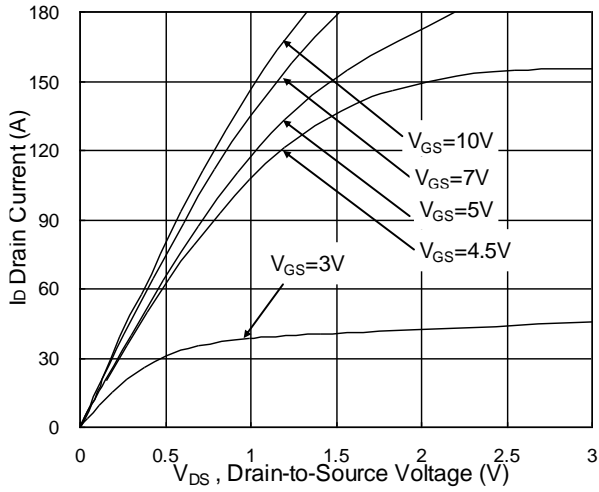


Fig.1 Typical Output Characteristics

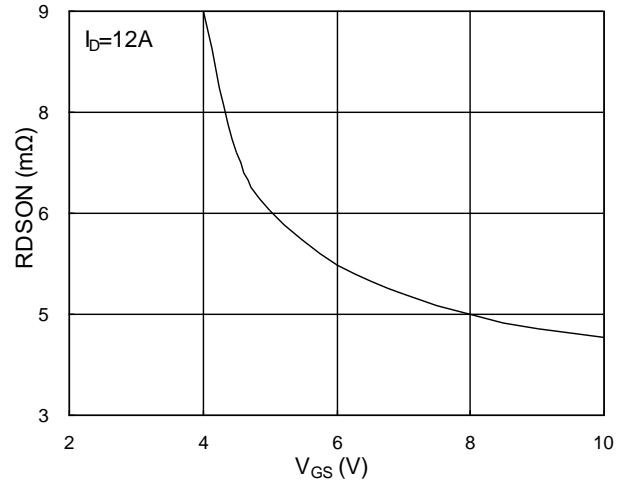


Fig.2 On-Resistance vs. G-S Voltage

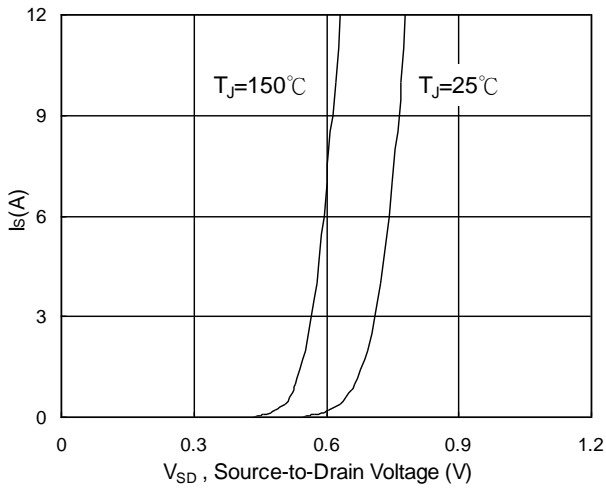


Fig.3 Forward Characteristics of Reverse

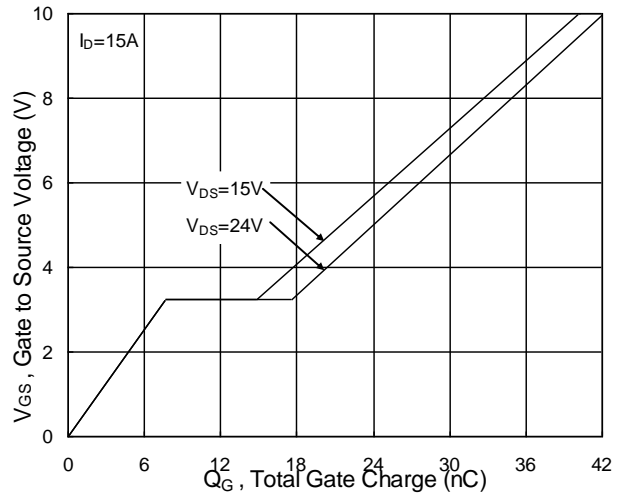


Fig.4 Gate-Charge Characteristics

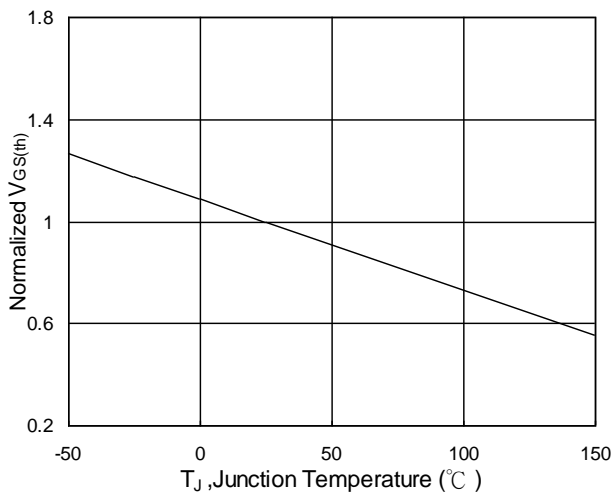


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

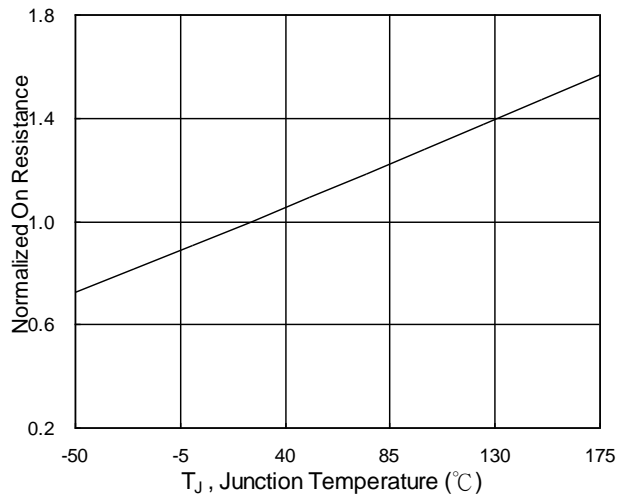


Fig.6 Normalized R_{DSON} vs. T_J

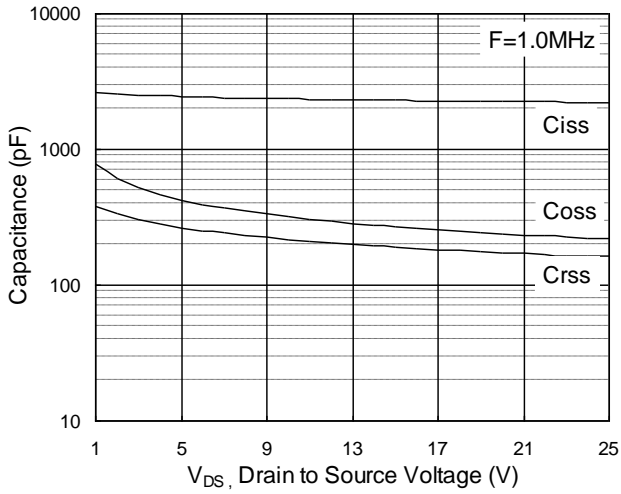


Fig.7 Capacitance

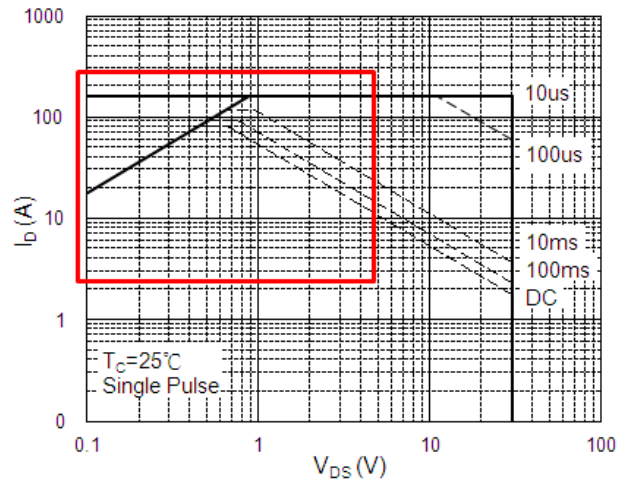


Fig.8 Safe Operating Area

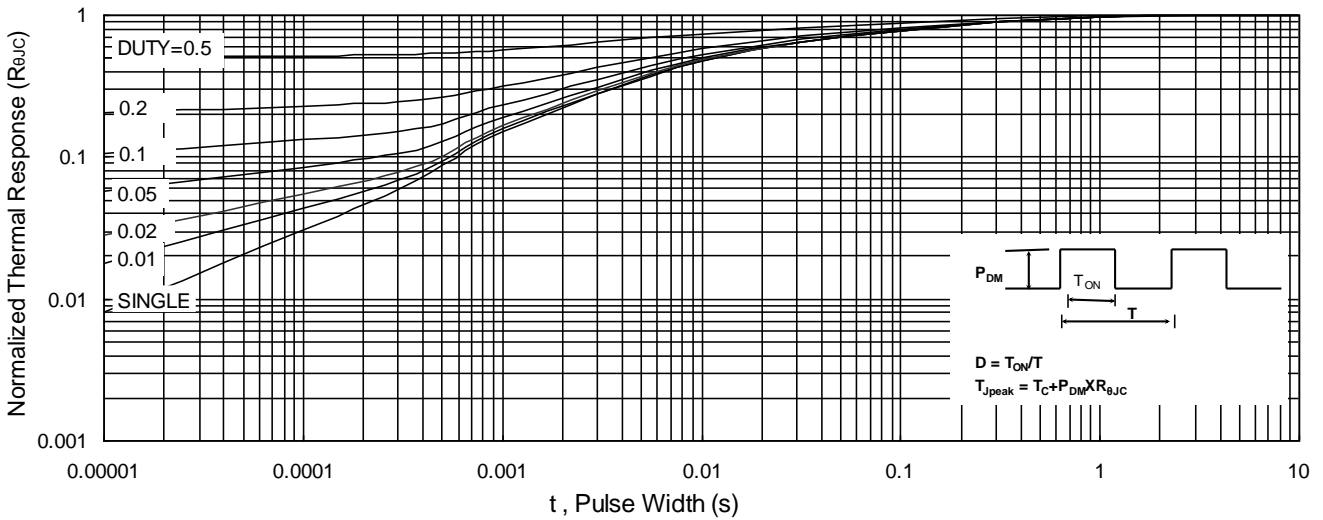


Fig.9 Normalized Maximum Transient Thermal Impedance

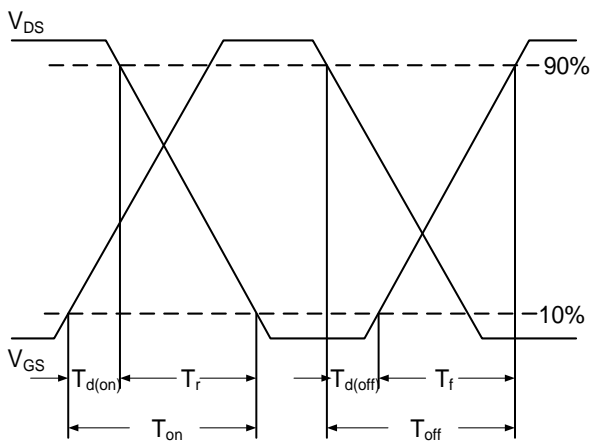


Fig.10 Switching Time Waveform

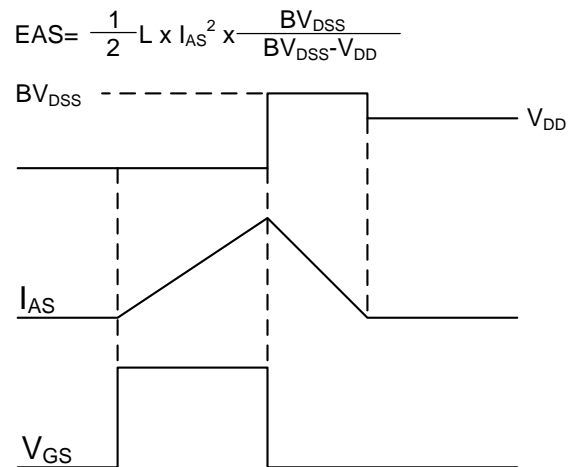
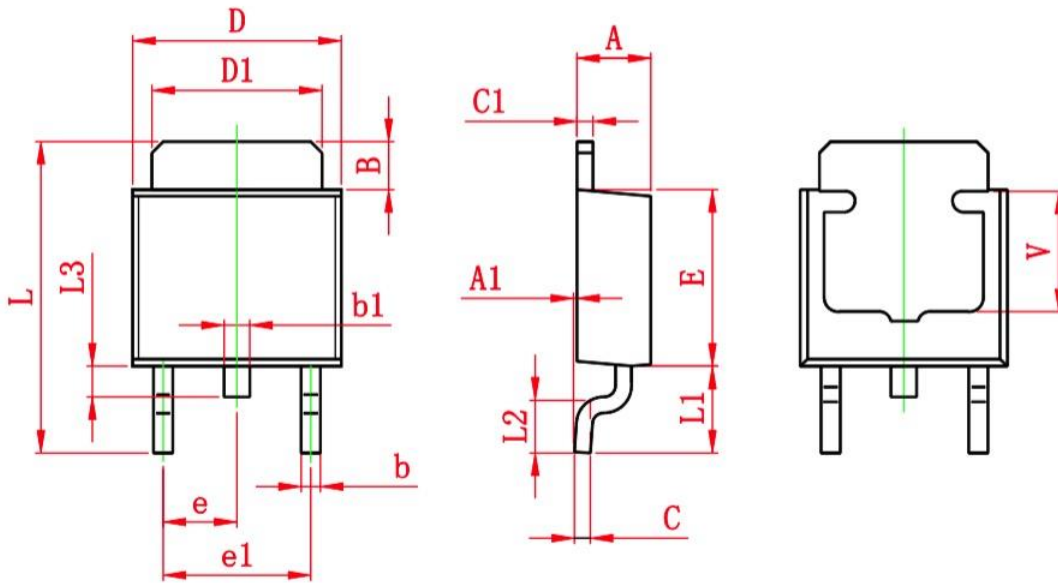


Fig.11 Unclamped Inductive Switching Waveform



Ordering Information

Part Number	Package code	Packaging
HSU80N03	TO252-2	2500/Tape&Reel



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP.		0.091 TYP.	
e1	4.500	4.700	0.177	0.185
L	9.500	9.900	0.374	0.390
L1	2.550	2.900	0.100	0.114
L2	1.400	1.780	0.055	0.070
L3	0.600	0.900	0.024	0.035
V	3.800 REF.		0.150 REF.	

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